

NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION

The **ASI BLX65S** is Designed for 12.5 V Class C Amplifier Applications in the 100 to 500 MHz Frequency Range.

FEATURES INCLUDE:

- Economical **TO-39** Package
- 8 dB Typical Gain
- Emitter Ballasting

MAXIMUM RATINGS

I_C	750 mA
V_{CBO}	36 V
P_{DISS}	5.0 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	$35^\circ C / W$

PACKAGE STYLE TO-39				
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
ϕa	0.190	0.210	4.83	5.33
A	0.240	0.260	6.10	6.60
ϕb	0.016	0.021	0.406	0.533
ϕb_2	0.016	0.019	0.406	0.483
ϕD	0.350	0.370	8.89	9.40
ϕD_1	0.315	0.335	8.00	8.51
h	0.009	0.125	0.229	3.18
i	0.028	0.034	0.711	0.864
k	0.029	0.040	0.737	1.02
l	0.500		12.70	
l_1		0.050		1.27
l_2	0.250		6.35	
P	0.100		2.54	
Q				
a	45° NOMINAL			
β	90° NOMINAL			

1 = EMITTER 2 = BASE
3 = COLLECTOR (CASE)

CHARACTERISTICS $T_A = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	16			V
BV_{CES}	$I_C = 50$ mA	36			V
BV_{EBO}	$I_E = 1.0$ mA	2.5			V
I_{CBO}	$V_{CB} = 15$ V			1.0	mA
h_{FE}	$V_{CB} = 5.0$ V $I_C = 50$ mA	20		200	---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		15		pF
G_{PE} η_C	$V_{CE} = 12.5$ V $P_{OUT} = 2.0$ W $f = 470$ MHz	7.0	55		dB %